

### 3-, 5-, and 10-A Power-Switching Transistors

High-Voltage N-P-N Type for Off-Line Power Supplies and Other High-Voltage Switching Applications

**Features:**

- 100% High Temperature Tested for 100°C Parameters
- Fast Switching Speed
- High voltage rating  
 $V_{CEX} = 350\text{ V}$   
 $= 450\text{ V [2N6545]}$
- Low  $V_{CE[sat]}$  at  $I_C = 3\text{-}, 5\text{-}, \text{ and } 10\text{-A}$

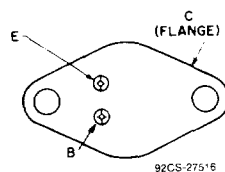
**Applications:**

- Off-Line Power Supplies
- High Voltage Inverters
- Switching Regulators

The 2N6542, 2N6544, 2N6545, and 2N6546 series of silicon n-p-n power transistors feature high-voltage capability, fast switching speeds, and low saturation voltages, together with high safe-operating-area (SOA) ratings. They are specially designed for off-line power supplies, converter circuits and pulse-width-modulated regulators. These high-voltage, high-speed transistors are 100-per-cent tested for parameters that are essential to the design of high-power switching circuits. Switching times, including inductive turn-off time, and saturation voltages are characterized at 100°C; as well as at 25°C, to provide information necessary for worst-case design.

The 2N6542, 2N6544, 2N6545, and 2N6546 transistors are supplied in steel JEDEC TO-204AA hermetic packages.

**TERMINAL DESIGNATIONS**



**JEDEC TO-204AA**

**MAXIMUM RATINGS, Absolute-Maximum Values:**

	2N6542	2N6544	2N6545	2N6546	
* $V_{CEV}$					
$V_{BE} \approx -1.5\text{ V}$ .....	650	650	850	650	V
* $V_{CEX}$ (Clamped)					
$V_{BE} \approx -1.5\text{ V}$ .....	350	350	450	350	V
* $V_{CEO}$ .....	300	300	400	300	V
* $V_{EBO}$ .....			8		V
$I_C$ (sat) .....	3	5	5	10	A
* $I_C$ .....	5	8	8	15	A
* $I_{CM}$ .....	10	16	16	30	A
* $I_B$ .....	5	8	8	10	A
* $P_T$					
$T_C$ up to 25°C .....	100	125	125	175	W
$T_C$ above 25°C, derate linearly .....	0.57	0.714	0.714	1	W/°C
* $T_{stg}, T_J$ .....		-65 to 200			°C
* $T_L$					
At distance $\geq 1/8$ in. (3.17 mm) from seating plane for 5 s max. ....		275			°C

\* In accordance with JEDEC registration data.

2N6542, 2N6544, 2N6545, 2N6546

ELECTRICAL CHARACTERISTICS Tc = 25° C

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POWER TRANSISTORS

CHARACTERISTIC	TEST CONDITIONS				LIMITS								UNITS	
	VOLTAGE V dc		CURRENT A dc		2N6542		2N6544		2N6545		2N6546			
	VCE	VBE	IC	IB	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
* ICEV	650 850	-1.5 -1.5	— —	— —	— —	0.5 —	— —	0.5 —	— —	— 0.5	— —	1 —	mA	
* IEBO	—	-8	0	—	—	1	—	1	—	1	—	1		
* VCEO(sus) <sup>b</sup>	—	—	0.1 <sup>a</sup>	—	300	—	300	—	400	—	300	—	V	
* hFE	2 2 3 3 2 2	— — — — — —	3 <sup>a</sup> 1.5 <sup>a</sup> 5 <sup>a</sup> 2.5 <sup>a</sup> 10 <sup>a</sup> 5 <sup>a</sup>	— — — — — —	7 12 — — — —	35 60 — — — —	— — 7 12 — —	— — 35 60 — —	— — 7 12 — —	— — 35 60 — —	— — — — — —	— — — — 6 12	— — — — 30 60	V
* VBE(sat)	— — —	— — —	3 <sup>a</sup> 5 <sup>a</sup> 10 <sup>a</sup>	0.6 1 2	— — —	1.4 — —	— — —	— 1.6 —	— — —	— 1.6 —	— — —	— — 1.6		
* VCE(sat)	— — — — —	— — — — —	3 <sup>a</sup> 5 <sup>a</sup> 8 <sup>a</sup> 10 <sup>a</sup> 15 <sup>a</sup>	0.6 1 2 2 3	— — — — —	1 5 — — —	— — — — —	— 1.5 5 — —	— — — — —	— 1.5 5 — —	— — — — —	— — — 1.5 5		
* IS/b t = 1 s	100	—	—	—	0.2	—	0.2	—	0.2	—	0.2	—	A	
* ft f = 1 MHz	10 10 10	— — —	0.2 0.3 0.5	— — —	6 — —	28 — —	— 6 —	— 28 —	— 6 —	— 28 —	— — 6	— — 28	MHz	
* Cobo f = 1 MHz	10 <sup>d</sup>	—	—	—	50	200	75	300	75	300	125	500	pF	
* td <sup>e,g</sup>	— — —	— — —	3 5 10	0.6 1 2	— — —	0.05 — —	— — —	— 0.05 —	— — —	— 0.05 —	— — —	— — 0.05	μS	
* tr <sup>e,g</sup>	— — —	— — —	3 5 10	0.6 1 2	— — —	0.7 — —	— — —	— 1 —	— — —	— 1 —	— — —	— — 1		
* ts <sup>e,g</sup>	— — —	— — —	3 5 10	0.6 1 2	— — —	4 — —	— — —	— 4 —	— — —	— 4 —	— — —	— — 4		
* tr <sup>e,g</sup>	— — —	— — —	3 5 10	0.6 1 2	— — —	0.8 — —	— — —	— 1 —	— — —	— 1 —	— — —	— — —		

\* In accordance with JEDEC registration data.

# 2N6542, 2N6544, 2N6545, 2N6546

ELECTRICAL CHARACTERISTICS  $T_c = 100^\circ\text{C}$

CHARACTERISTIC	TEST CONDITIONS				LIMITS								UNITS
	VOLTAGE V dc		CURRENT A dc		2N6542		2N6544		2N6545		2N6546		
	VCE	VBE	IC	IB	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
* ICEV	650	-1.5	—	—	—	2.5	—	2.5	—	—	—	4	mA
	850	-1.5	—	—	—	—	—	—	—	2.5	—	—	
* ICER RBE = 50 $\Omega$	650	—	—	—	—	3	—	3	—	—	—	5	mA
	850	—	—	—	—	—	—	—	—	3	—	—	
* VCEX(sus) <sup>b,c</sup> VCC = 20 V L = 180 $\mu\text{H}$ , RC = 0.05 $\Omega$ Vclamp = Rated VCEX	—	—	2.6 <sup>a</sup>	—	350	—	—	—	—	—	—	—	V
	—	—	4.5 <sup>a</sup>	—	—	—	350	—	450	—	—	—	
	—	—	8 <sup>a</sup>	—	—	—	—	—	—	—	350	—	
	—	—	8 <sup>a</sup>	—	200	—	—	—	—	—	—	—	
* VBE(sat)	—	—	3 <sup>a</sup>	0.6	—	1.4	—	—	—	—	—	—	V
	—	—	5 <sup>a</sup>	1	—	—	—	1.6	—	1.6	—	—	
	—	—	10 <sup>a</sup>	2	—	—	—	—	—	—	—	1.6	
* VCE(sat)	—	—	3 <sup>a</sup>	0.6	—	2	—	—	—	—	—	—	V
	—	—	5 <sup>a</sup>	1	—	—	—	2.5	—	2.5	—	—	
	—	—	10 <sup>a</sup>	2	—	—	—	—	—	—	—	2.5	
* ts <sup>f,g</sup>	—	-5	3	0.6	—	4	—	—	—	—	—	—	$\mu\text{S}$
	—	-5	5	1	—	—	—	4	—	4	—	—	
	—	-5	10	2	—	—	—	—	—	—	—	5	
* tf <sup>f,g</sup>	—	-5	3	0.6	—	0.8	—	—	—	—	—	—	$\mu\text{S}$
	—	-5	5	1	—	—	—	0.9	—	0.9	—	—	
	—	-5	10	2	—	—	—	—	—	—	—	1.5	
* R $\theta$ JC	—	—	—	—	—	1.75	—	1.4	—	1.4	—	1	$^\circ\text{C/W}$

\* In accordance with JEDEC registration data.

<sup>a</sup> Pulsed: pulse duration = 300  $\mu\text{s}$ , duty factory  $\leq 2\%$ .

**bCAUTION:** The sustaining voltage VCE0(sus) and VCEX(sus) *MUST NOT* be measured on a curve tracer.

<sup>c</sup> VCC = 20 V, L = 180  $\mu\text{H}$ , RC = 0.05  $\Omega$

<sup>d</sup> VCB value

<sup>e</sup> Resistive load, VCC = 250 V, tp = 100  $\mu\text{s}$ , IB1 = -IB2

<sup>f</sup> Inductive load, Vclamp = Rated VCEX(sus), IB1 = -IC/5, L = 180  $\mu\text{H}$ , RC = 0.05  $\Omega$ , VCC = 20 V

<sup>g</sup> For switching speed test methods, see Application Note AN-6820.

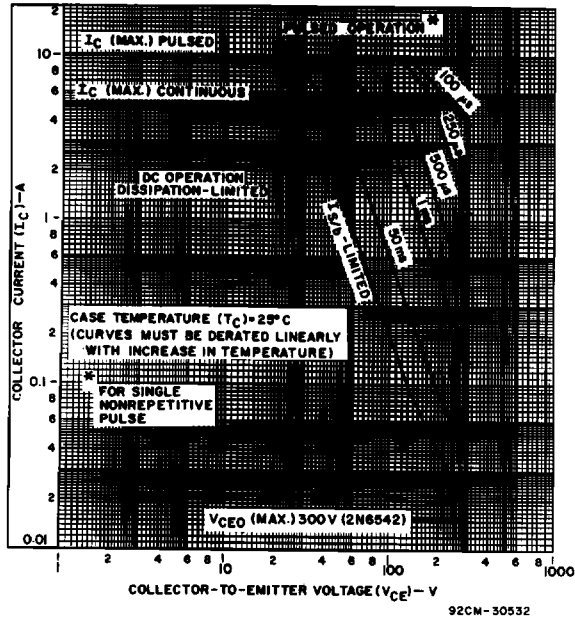


Fig. 1 - Maximum operating areas for type 2N6542 ( $T_C = 25^\circ$ ).

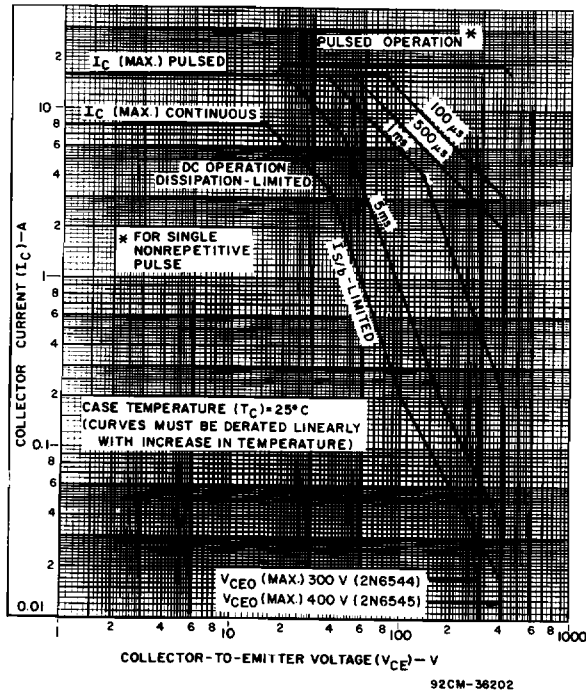


Fig. 2 - Maximum operating areas for type 2N6544 and 2N6545 ( $T_C = 25^\circ$  C).

2N6542, 2N6544, 2N6545, 2N6546

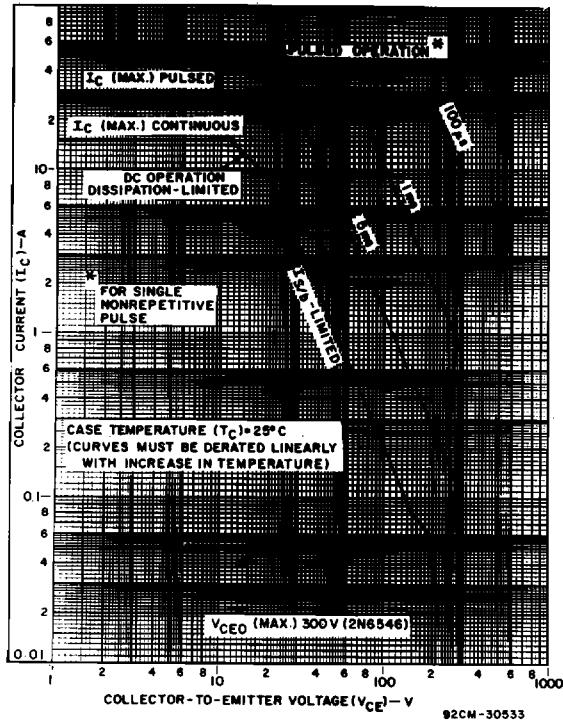


Fig. 3 - Maximum operating areas for type 2N6546 ( $T_c = 25^\circ$ )

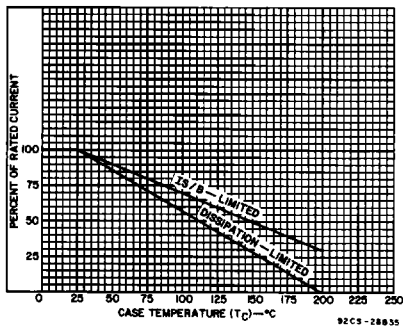


Fig. 4 - Dissipation and  $I_{S/B}$  derating curves for all types.

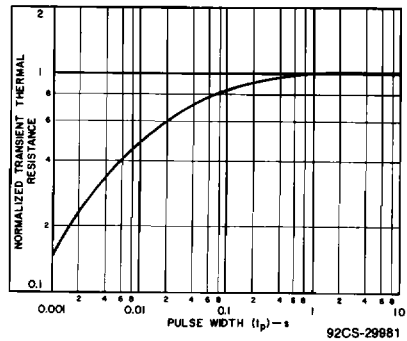


Fig. 5 - Typical thermal-response characteristics for types 2N6542, 2N6544 and 2N6545.

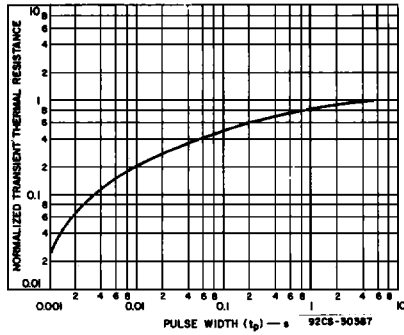


Fig. 6 — Typical thermal-response characteristics for type 2N6546.

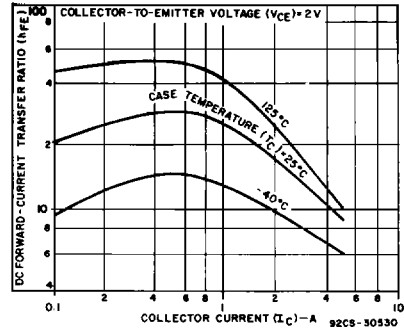


Fig. 7 — Typical dc beta characteristics for type 2N6542.

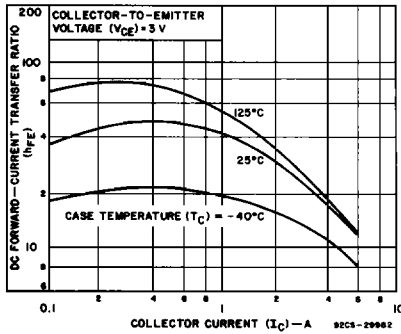


Fig. 8 — Typical dc beta characteristics for type 2N6544.

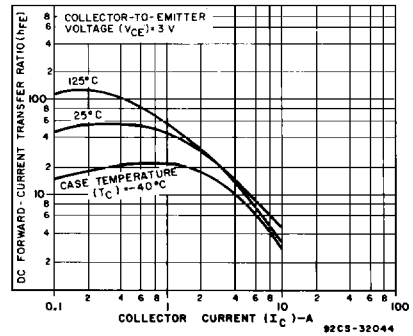


Fig. 9 — Typical dc beta characteristics for type 2N6545.

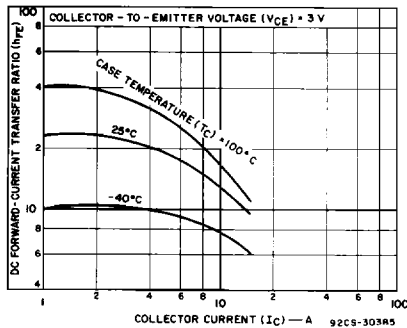


Fig. 10 — Typical dc beta characteristics for type 2N6546.

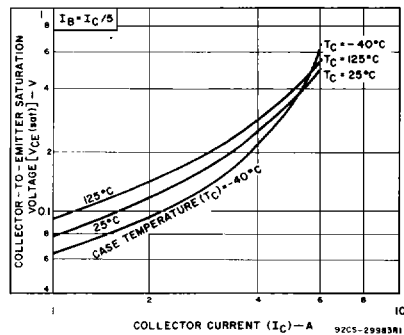


Fig. 11 — Typical collector-to-emitter saturation voltage as a function of collector current for types 2N6542 and 2N6544.

# 2N6542, 2N6544, 2N6545, 2N6546

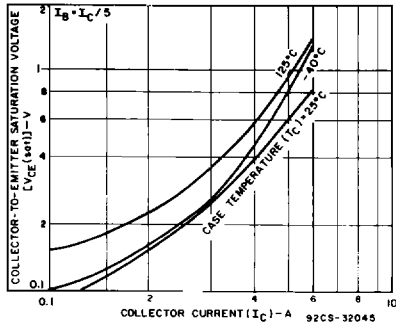


Fig. 12 — Typical collector-to-emitter saturation voltage as a function of collector current for type 2N6545.

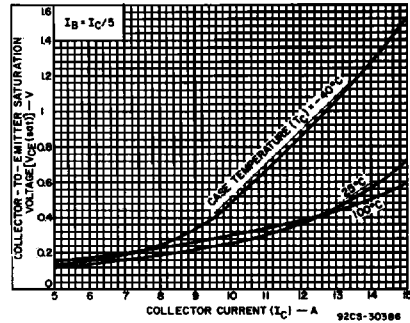


Fig. 13 — Typical collector-to-emitter saturation voltage characteristics for type 2N6546.

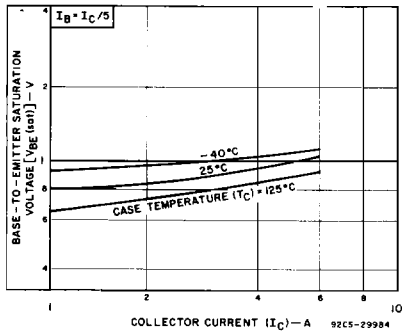


Fig. 14 — Typical base-to-emitter saturation voltage as a function of collector current for types 2N6542 and 2N6544.

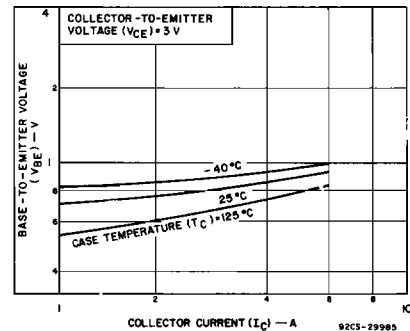


Fig. 15 — Typical base-to-emitter voltage as a function of collector current for types 2N6542 and 2N6544.

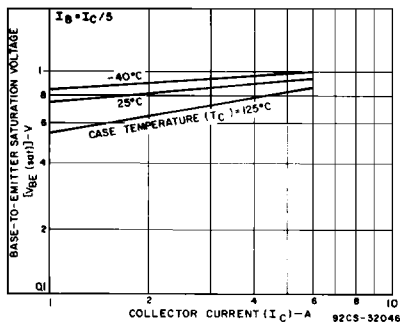


Fig. 16 — Typical base-to-emitter saturation voltage as a function of collector current for type 2N6545.

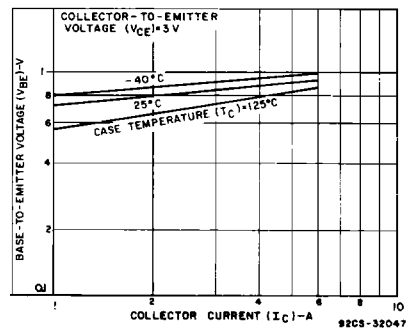


Fig. 17 — Typical base-to-emitter voltage as a function of collector current for type 2N6545.

# 2N6542, 2N6544, 2N6545, 2N6546

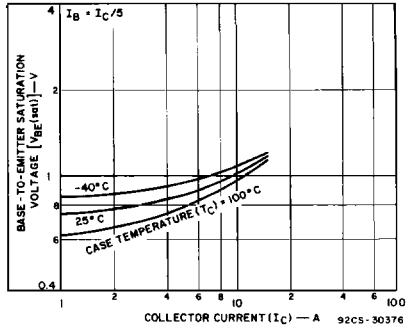


Fig. 18 — Typical base-to-emitter saturation voltage characteristics for type 2N6546.

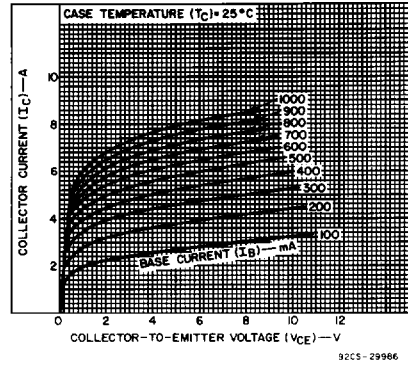


Fig. 19 — Typical output characteristics for types 2N6542 and 2N6544.

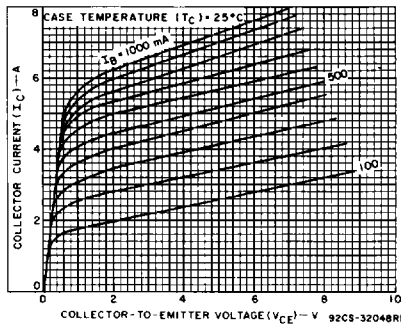


Fig. 20 — Typical output characteristics for type 2N6545.

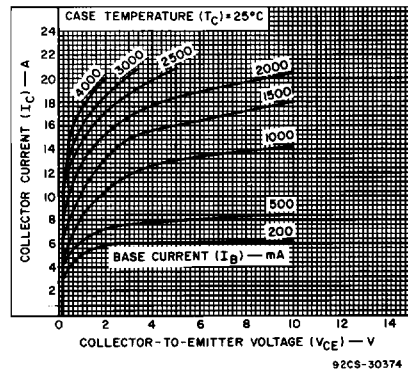


Fig. 21 — Typical output characteristics for type 2N6546.

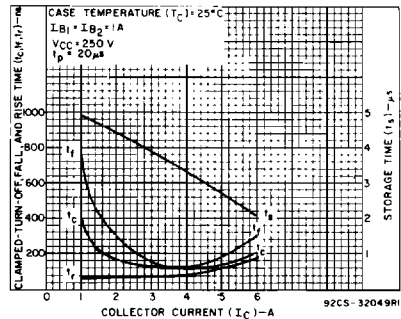


Fig. 22 — Typical saturated switching time characteristics for type 2N6545.

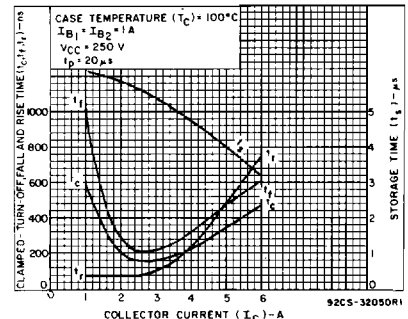


Fig. 23 — Typical saturated switching time characteristics for type 2N6546.

2  
POWER TRANSISTORS



# 2N6542, 2N6544, 2N6545, 2N6546

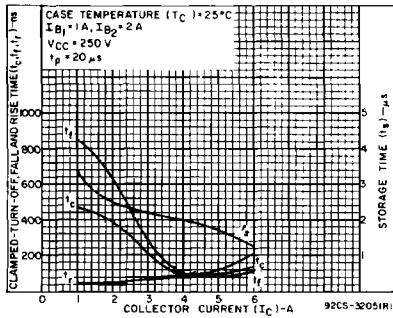


Fig. 24 — Typical saturated switching time characteristics for type 2N6545.

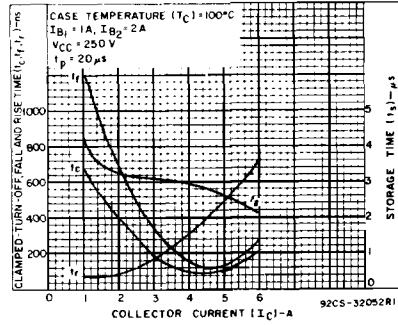


Fig. 25 — Typical saturated switching time characteristics for type 2N6545.

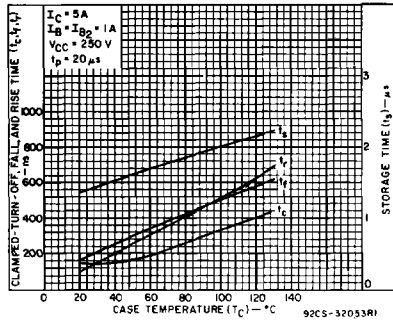


Fig. 26 — Typical saturated switching time characteristics as a function of case temperature for type 2N6545.

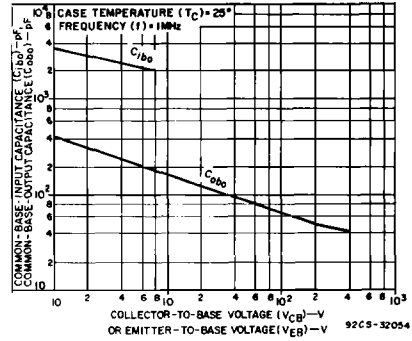


Fig. 27 — Typical common-base input or output capacitance characteristics as a function of collector-to-base voltage or emitter-to-base voltage for type 2N6545.